

## FQD3P50TM

# Power MOSFET, P-Channel, QFET<sup>®</sup>, -500 V, -2.1 A, 4.9 $\Omega$ , DPAK

## Product Overview

For complete documentation, see the data sheet.

This P-Channel enhancement mode power MOSFET is produced using a proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

## Features

- -2.1A, -500V,  $R_{DS(on)} = 4.9\Omega$  (Max.) @VGS = 10 V, ID = -1.05A
- Low gate charge (Typ. 18nC)
- Low Crss (Typ. 9.5pF)
- 100% avalanche tested

## Applications

- Lighting